

Title (en)

METHOD FOR LATERAL SEPARATION OF A SEMICONDUCTOR WAFER STACK

Title (de)

VERFAHREN ZUM LATERALEN ZERTRENNEN EINES HALBLEITERSTAPELWAFERS

Title (fr)

PROCÉDÉ POUR SÉPARER LATÉRALEMENT UNE PLAQUETTE DE SEMI-CONDUCTEURS EMPILÉS

Publication

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Application

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Abstract (en)

[origin: WO2007025499A1] The inventive method for laterally cutting through a semiconductor wafer (1) comprises the following steps: - a growth substrate (2) is prepared, - a semiconductor layer sequence (3), which comprises a functional semiconductor layer, is epitaxially grown on the growth substrate (2), - a masking layer (10) is applied to a partial area of the semiconductor layer sequence (3) in order to produce masked areas (11) and unmasked areas (12), - ions are implanted through the unmasked areas (12) in order to produce implantation areas (13) in the semiconductor wafer (1), and the semiconductor wafer (1) is cut through along the implantation area (13). The growth substrate (2) or at least one part of the growth substrate (2) is separated from the semiconductor wafer.

IPC 8 full level

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CPC (source: EP US)

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